

FIG. 1

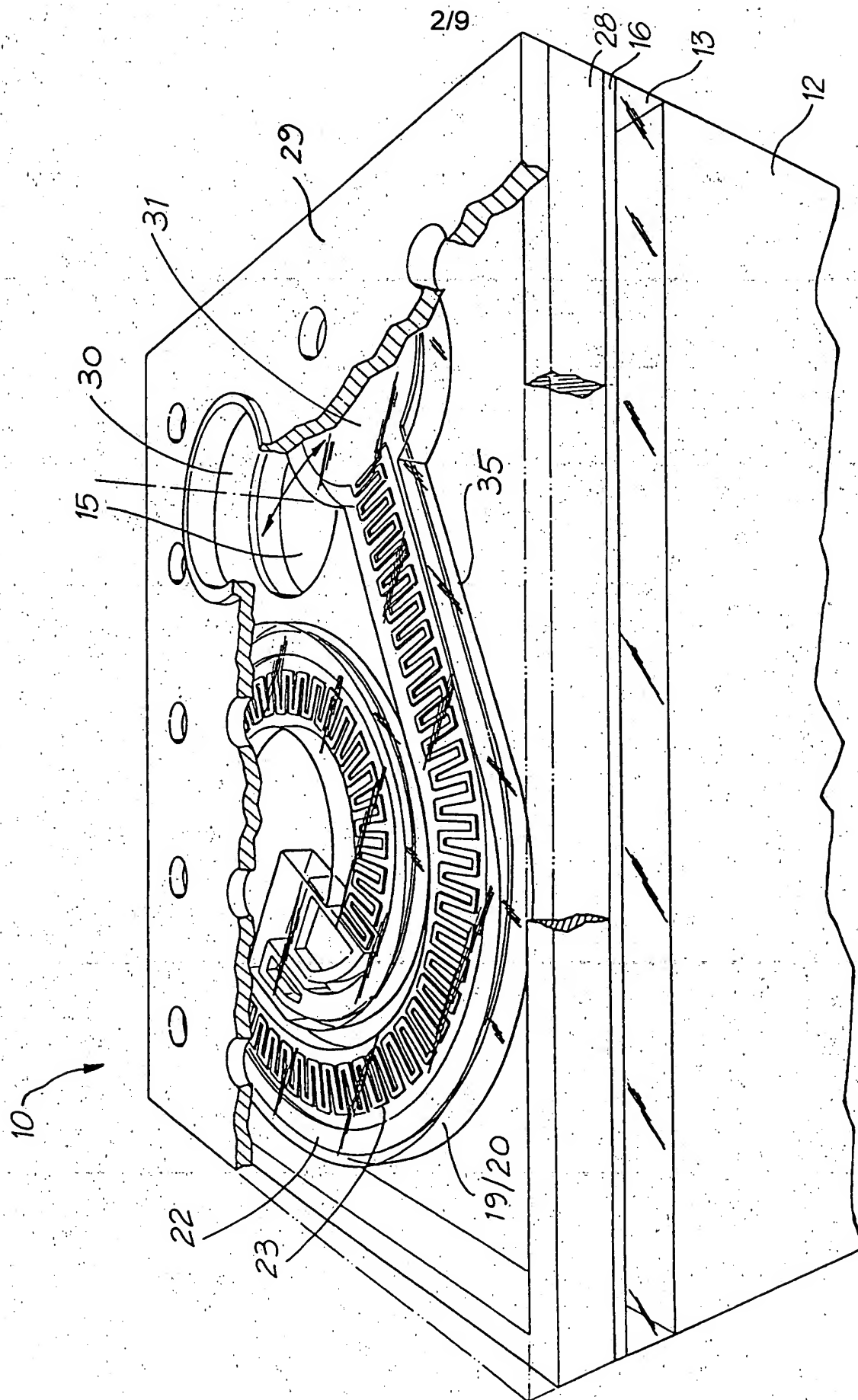


FIG. 2



























	Silicon		Sacrificial material		Elastomer
	Boron doped silicon		Cupronickel		Polyimide
	Silicon nitride (Si_3N_4)		CoNiFe or NiFe		Indium tin oxide (ITO)
	CMOS device region		Permanent magnet		PTFE
	Aluminum		Polysilicon		Conductive PTFE
	Glass (SiO_2)		Titanium Nitride (TiN)		Terfenol-D
	Copper		Titanium boride (TiB_2)		Shape memory alloy
	Gold		Adhesive		Tantalum
			Resist		Ink

FIG. 3

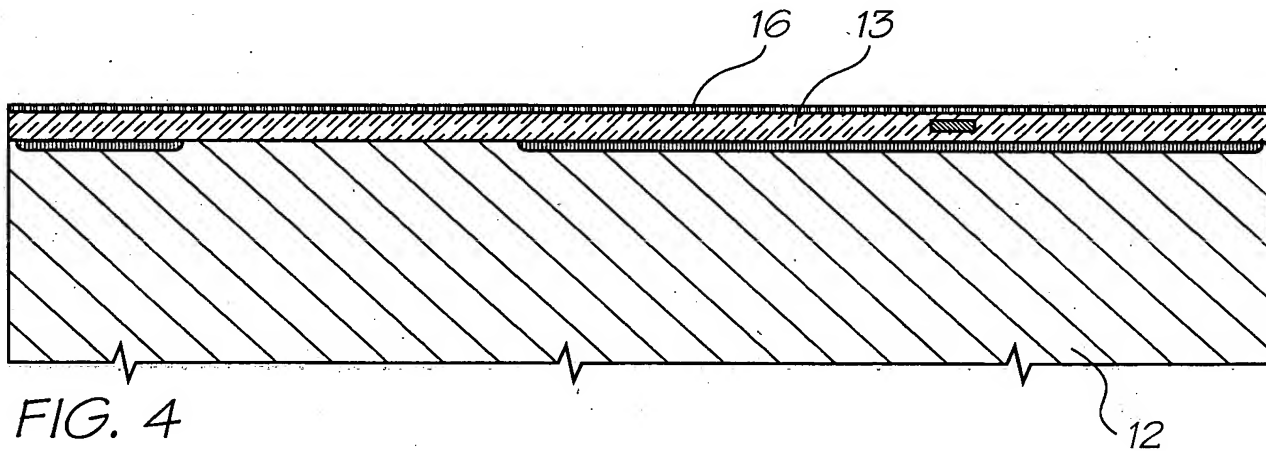


FIG. 4

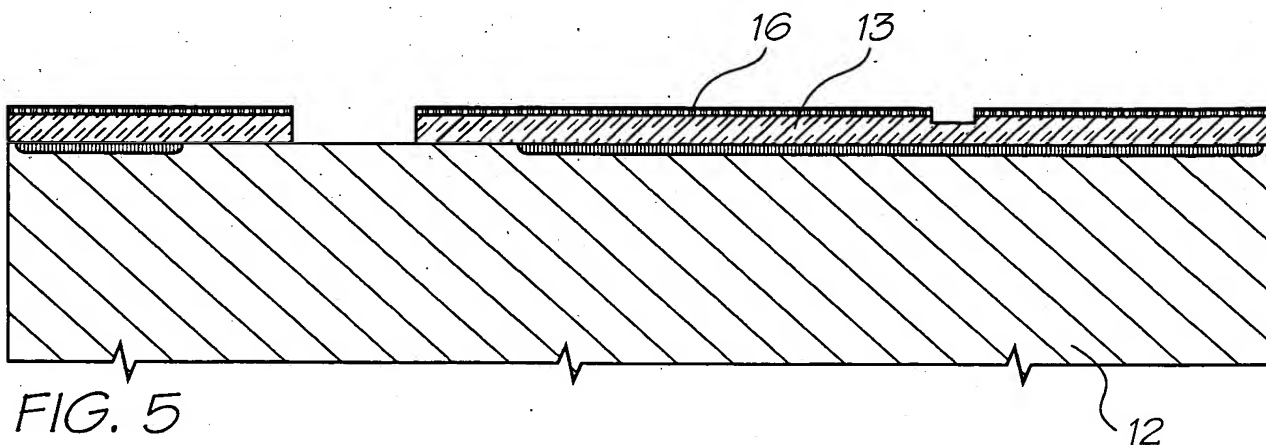
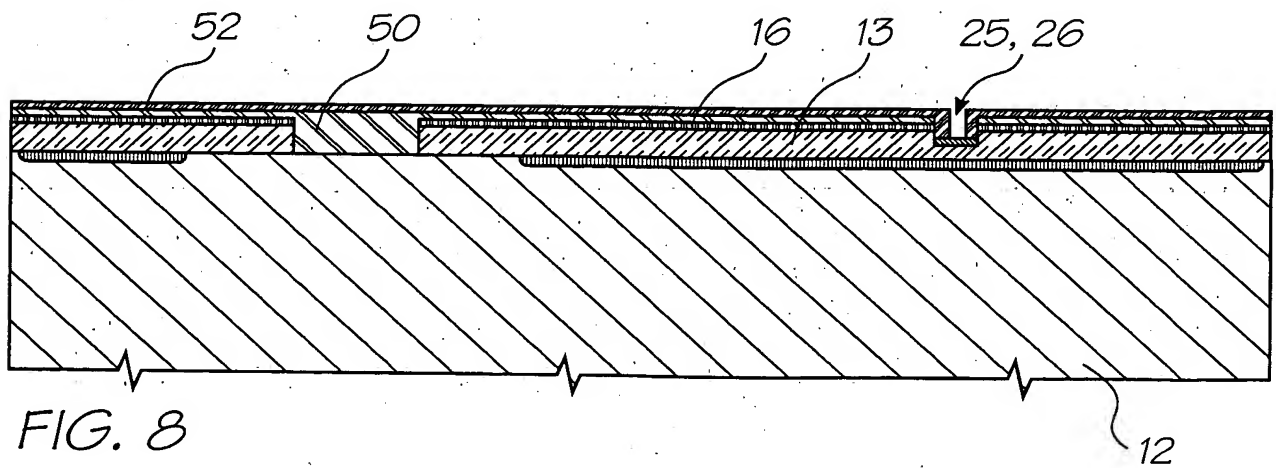
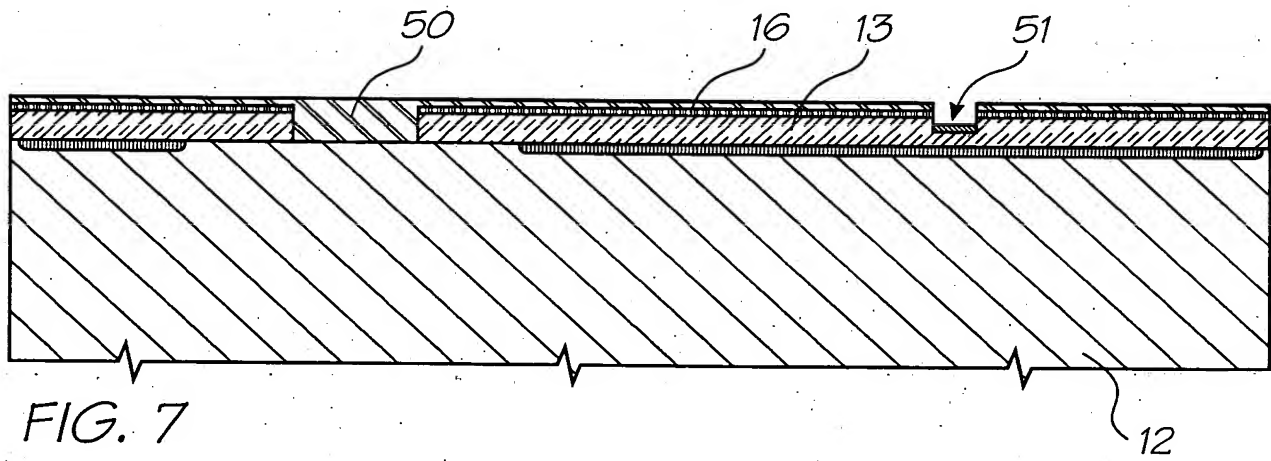
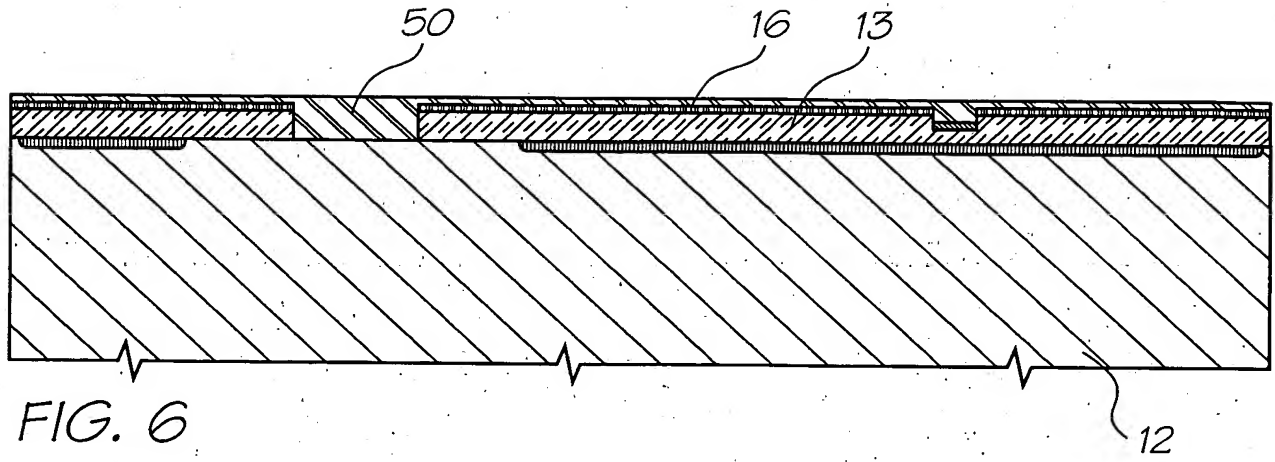
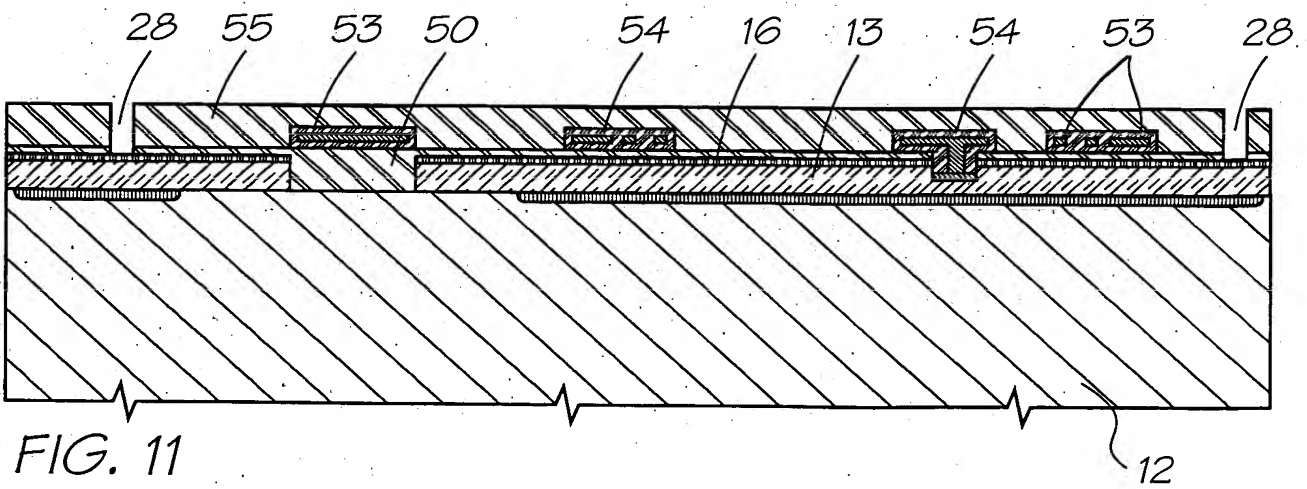
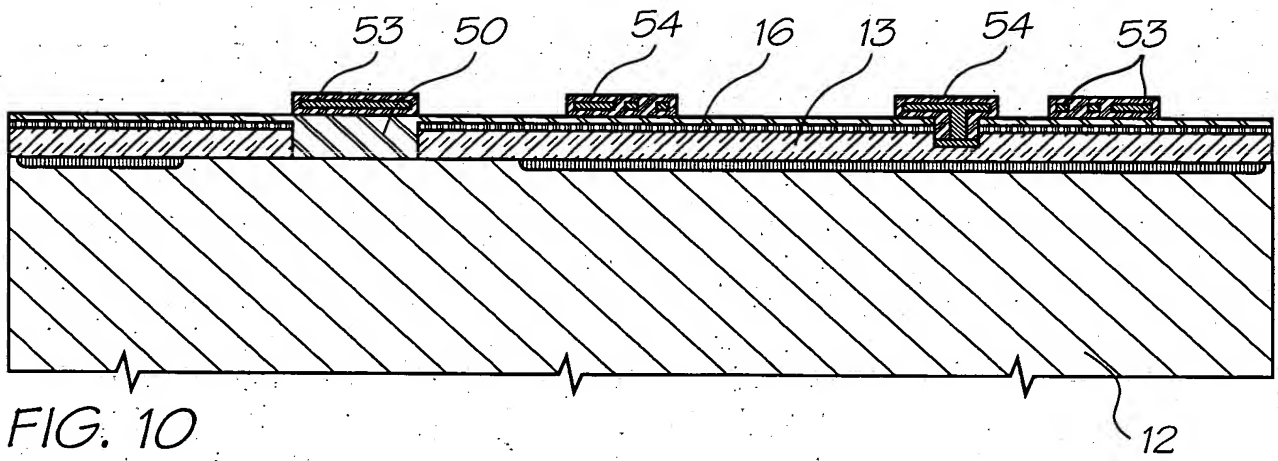
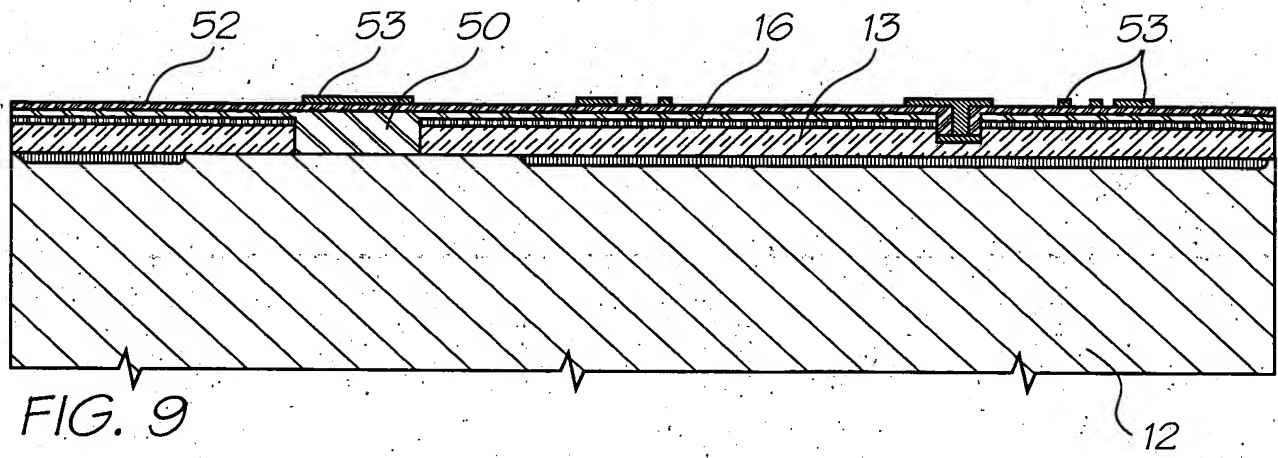
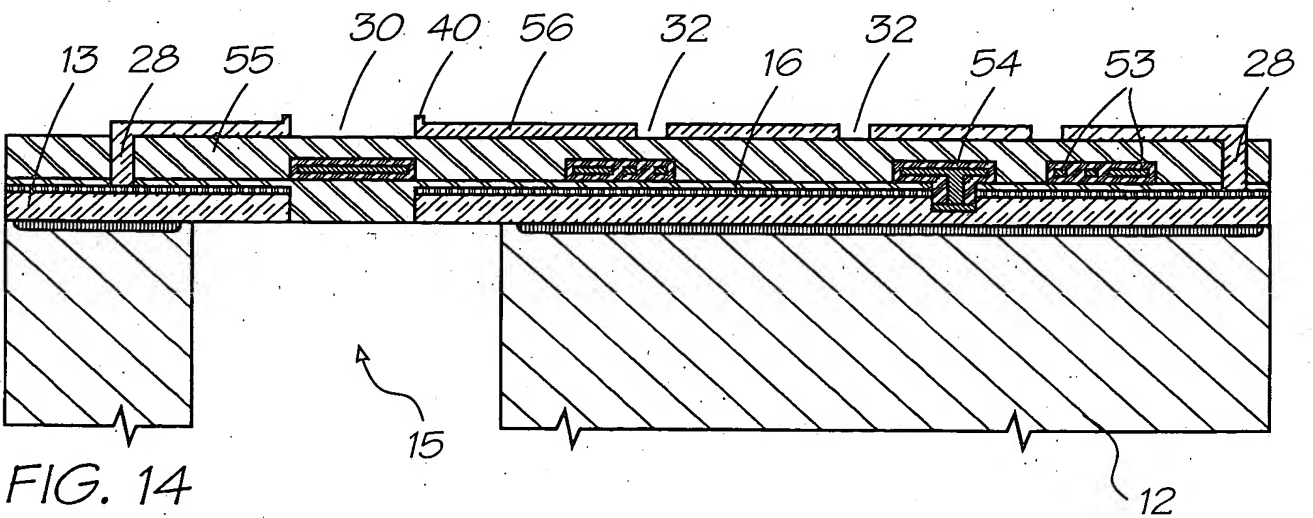
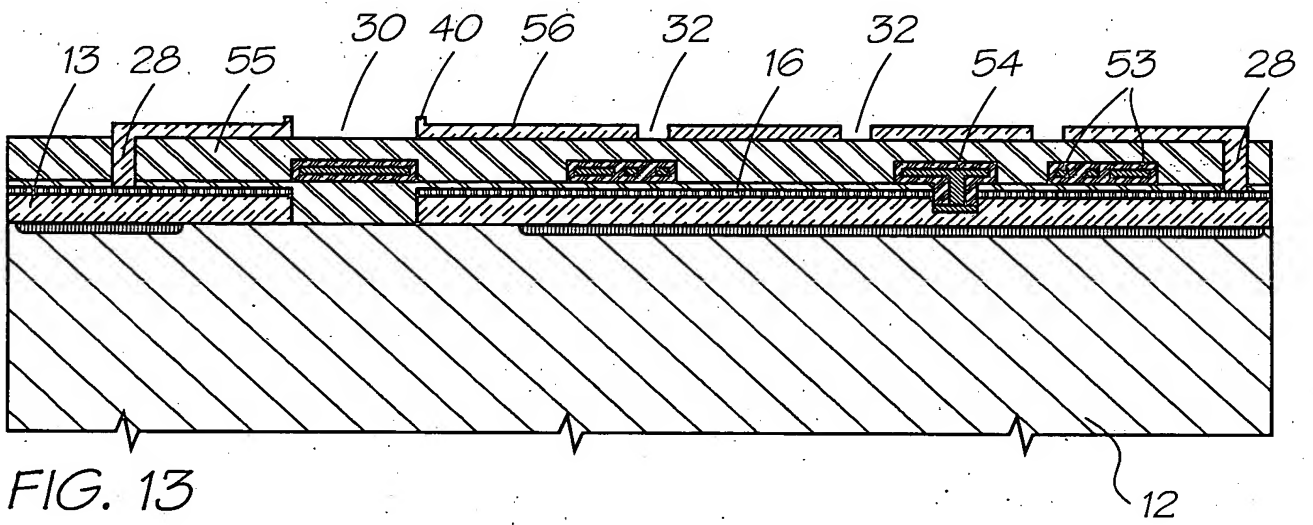
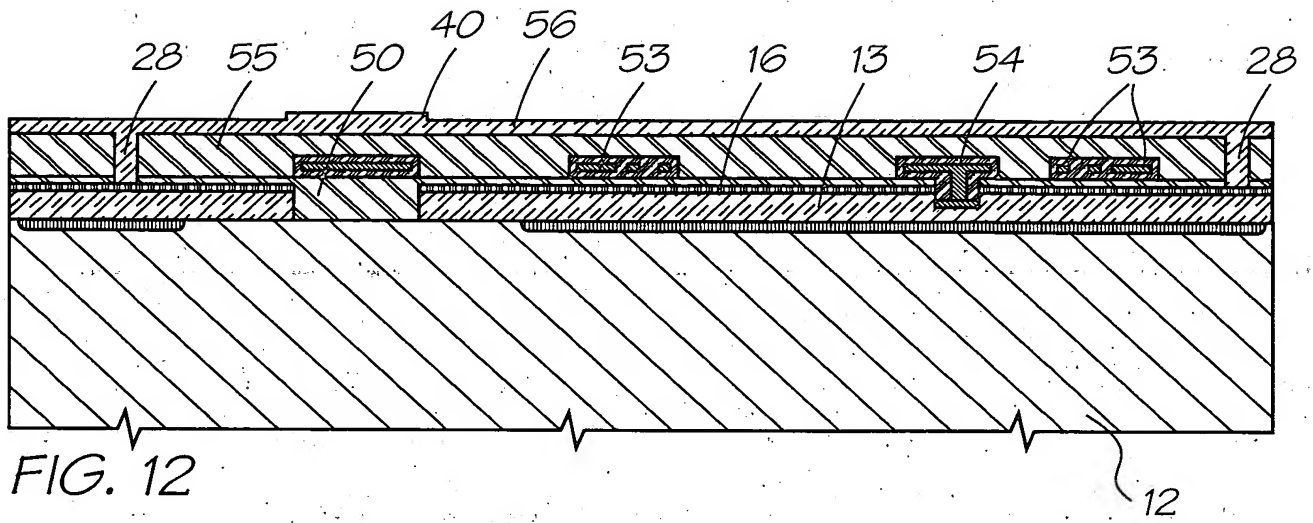
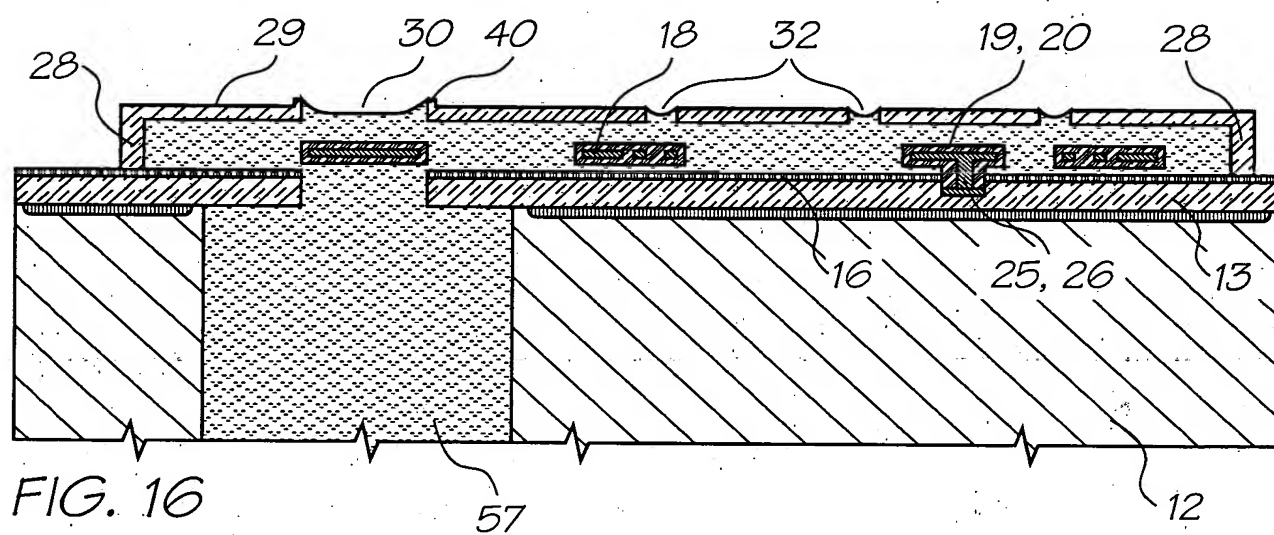


FIG. 5









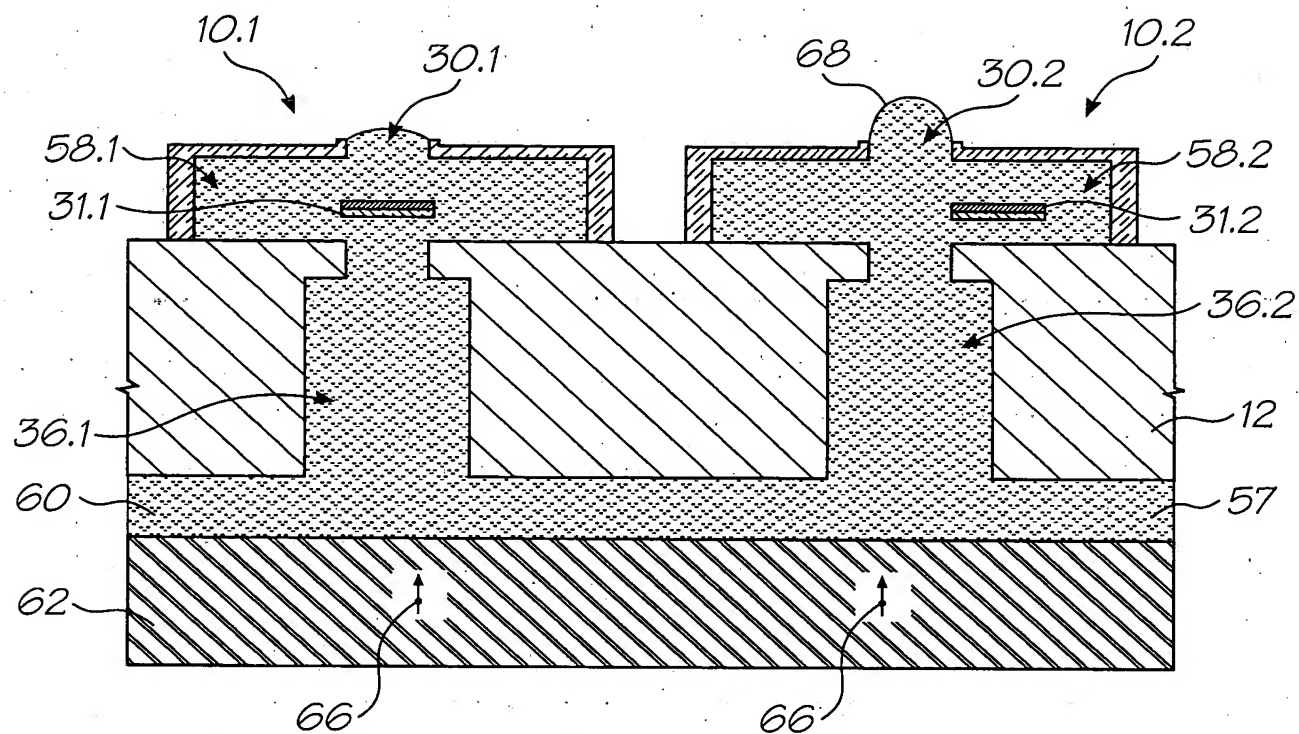


FIG. 17

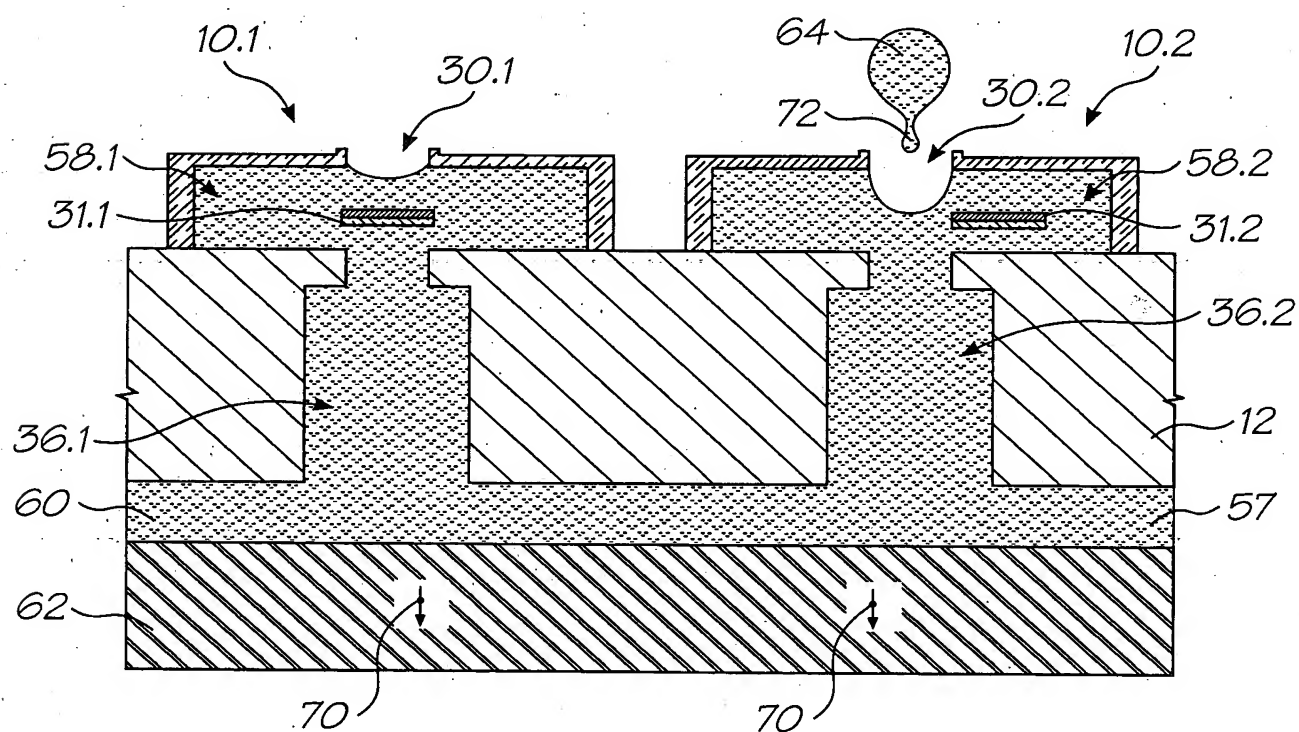


FIG. 18

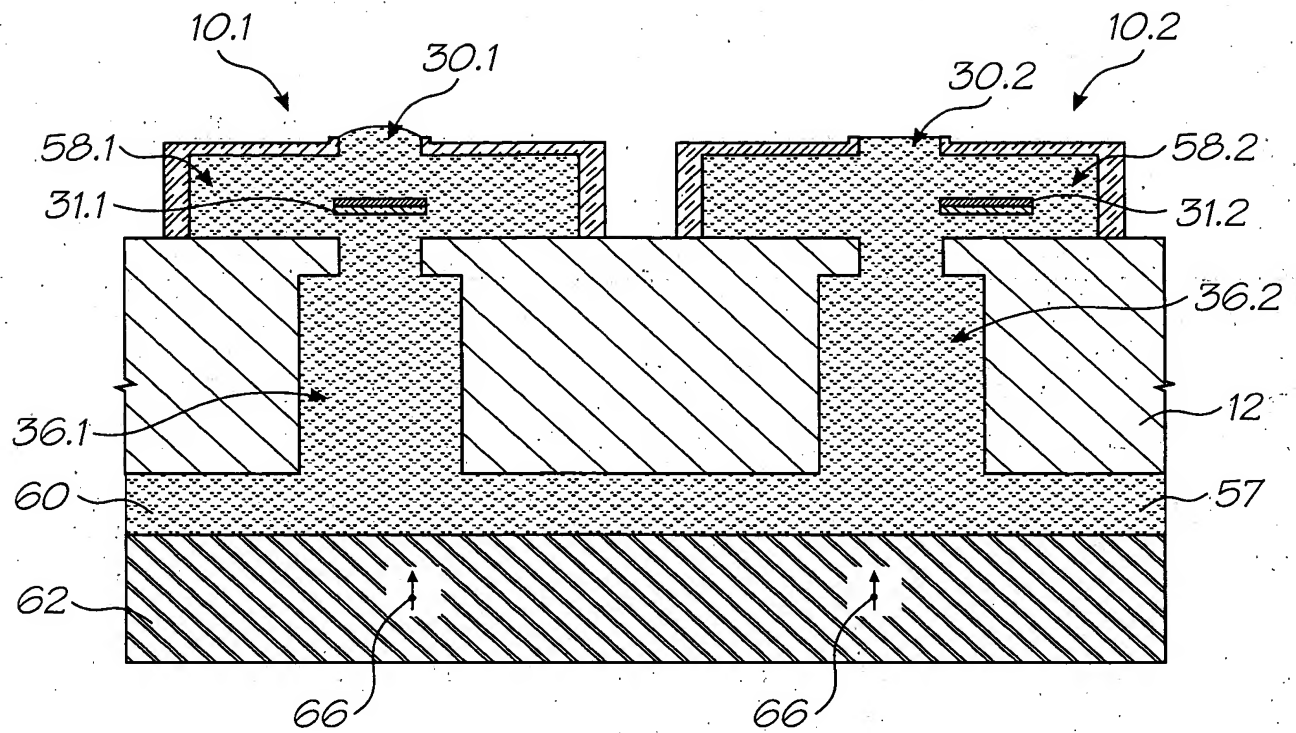


FIG. 19

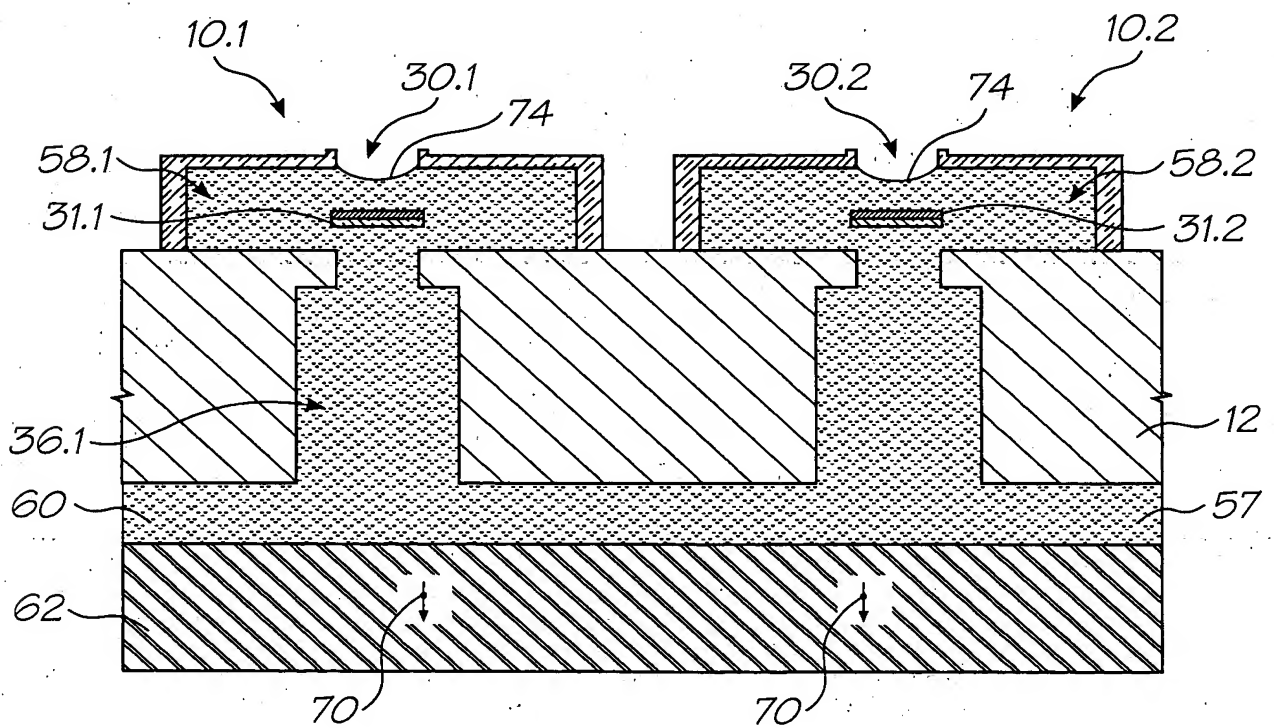


FIG. 20